MY25N50F

500V N-Channel Enhancement Mode MOSFET

MAOYUANWEI semiconductor

General Description

The MY25N50F uses advanced trench technology and design to provide excellent RDS(ON) with low gate Charge It can be used in a wide variety of application

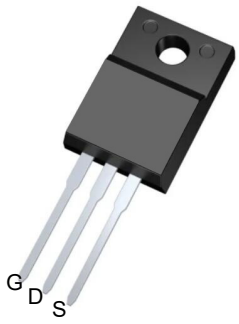
RoHS Compliant

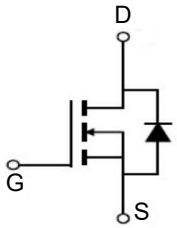
Features

V_{DSS}	500	V
I_D	25	A
P_D(T_C=25℃)	45	W
$R_{DS(ON)}$(atV_{GS} = 10V)	176	mΩ

Application

- Power switching application.
- Hard switched and high frequency circuits.
- Uninterruptible power supply.





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY25N50F	TO-220F	MY25N50F	1000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain- Source Voltage	500	V
V_{GS}	Gate Source Voltage	±30	V
I_D@ T_C=25℃	Continuous Drain Current[1]	25	A
I_D@T_C=100℃	Continuous Drain Current[1]	15	A
I_{DM}	Pulsed Drain Current[3]	44	A
E_{AS},E_{AR}	Avalanche Energy[5]	3.8	mJ
I_{AS},I_{AR}	Avalanche Current[5]	3.9	A
P_D@ T_C=25℃	Total Power Dissipation[4]	45	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JC}$	Thermal Resistance, Junction- to- Case[2]	3	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [2]	62	℃/W

Electrical Characteristics (T_C=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250uA	500	--	--	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V,I_D=5A	170	--	180	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS},I_D=250uA	2	--	4	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=500V,V_{GS}=0V,T_J=25℃	---	---	1	uA
		V_{DS}=400V,V_{GS}=0V,T_J=100℃	---	---	10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V,V_{DS}=0V	---	---	±100	nA
g_{FS}	Forward Transconductance	V_{DS}=10V,I_D=10A	---	4	---	S
Q_g	Total Gate Charge	V_{DS}=400V,V_{GS}=10V,I_D=2A	---	37	60	nC
Q_{gs}	Gate-Source Charge		---	11	20	
Q_{gd}	Gate-Drain Charge		---	12	24	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=300V,I_{DS}=1A, V_{GEN}=10V,R_G=25 Ω	---	18	36	nS
T_r	Rise Time		---	25	50	
$T_{d(off)}$	Turn-Off Delay Time		---	42	84	
T_f	Fall Time		---	68	136	
C_{iss}	Input Capacitance	V_{DS}=30V,V_{GS}=0V,f=1MHz	---	352	700	pF
C_{oss}	Output Capacitance		---	25	50	
C_{rss}	Reverse Transfer Capacitance		---	2.5	5	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Curren[1,4]	VG=VD=0V	---	---	20	A
I_{SM}	Pulsed Source Current		---	---	20	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V,I_{SD}=10A,T_J=25℃	---	---	0.8	V
T_{rr}	Reverse Recovery Time	I_S=5A,V_{GS}=0V, di/dt=100A/μsTJ=25℃	---	135	---	nS
Q_{rr}	Reverse Recovery Charge		---	0.37	---	uC

Notes:

1 . Repetitive Rating: Pulse width limited by maximum junction temperature.
2 . Surface Mounted on FR4 Board, t ≤ 1 0 sec.
3 . Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤2 %.
4 . The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.
5 . The EAS test condition is VDD =30V,VGS =10V,L=0.5mH,IAS =3.9A

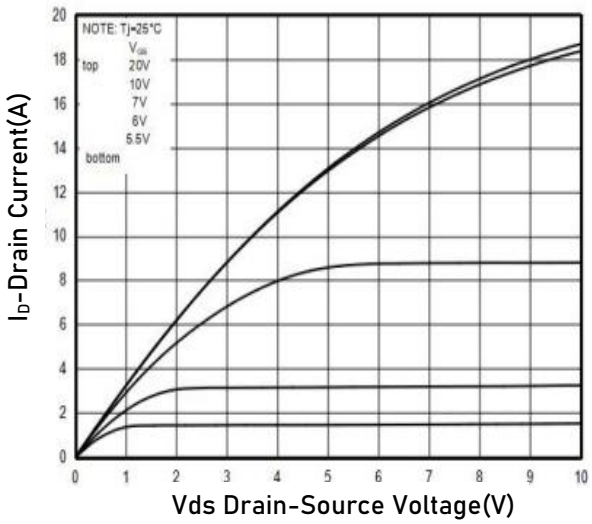


Fig.1 Typical Output Characteristics

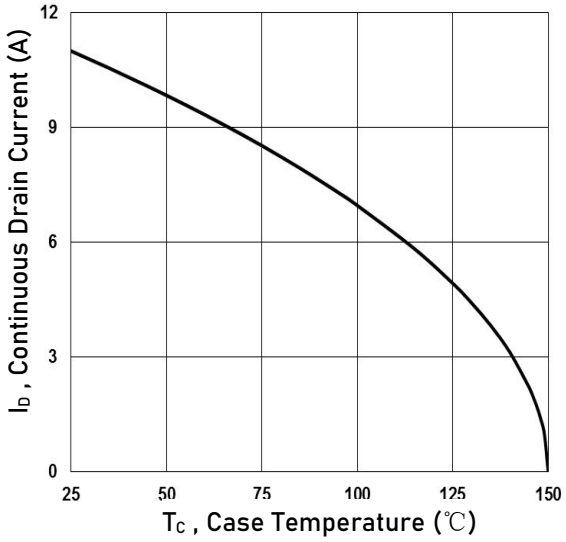


Fig.2 Drain Current

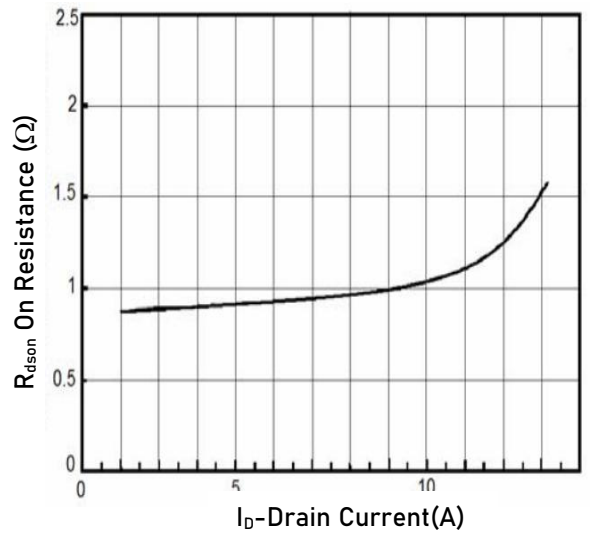


Fig.3 Drain-Source On Resistance

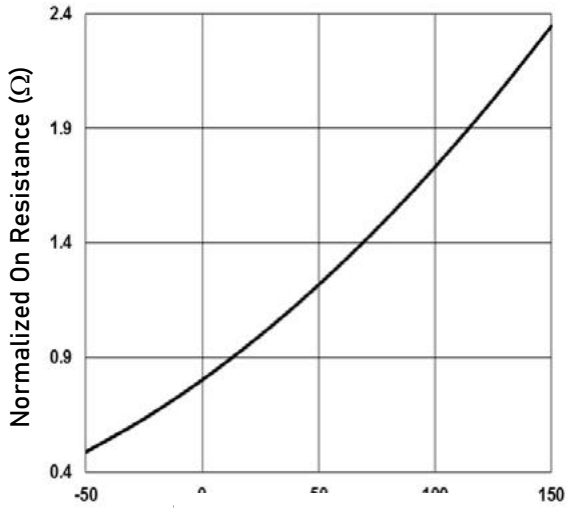


Fig.4 Normalized RDSON vs. T_J

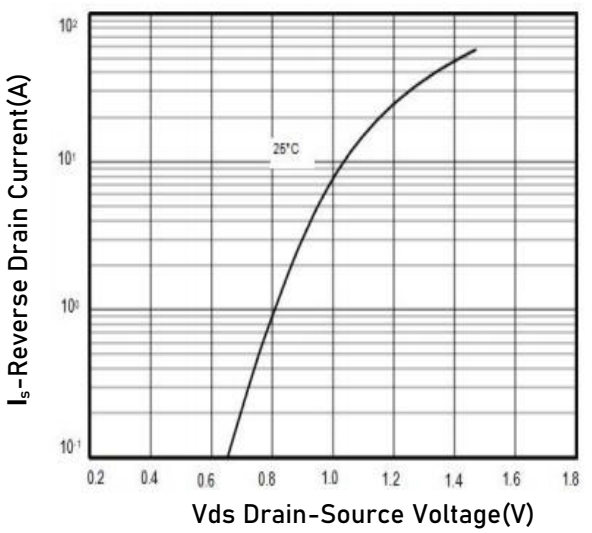


Fig.5 Forward Characteristics Of Reverse

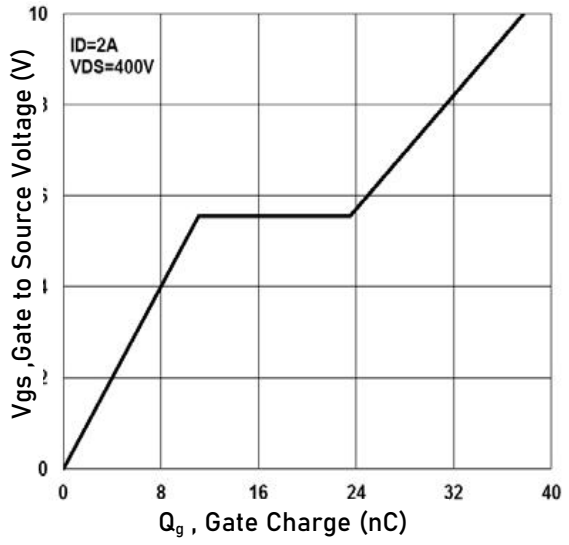


Fig.6 Gate-Charge Characteristics

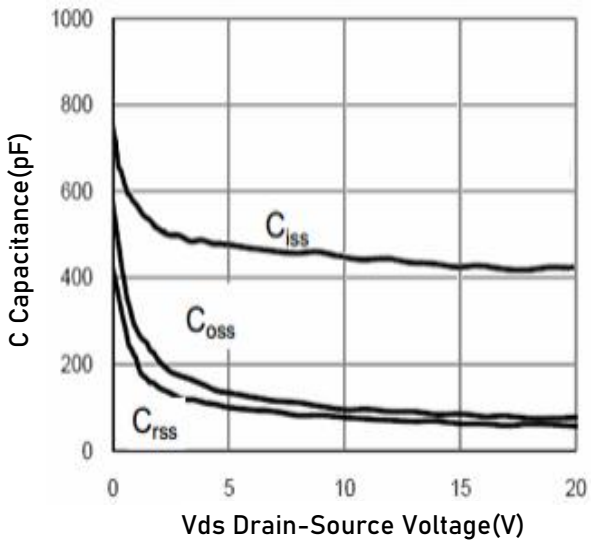


Fig.7 Capacitance

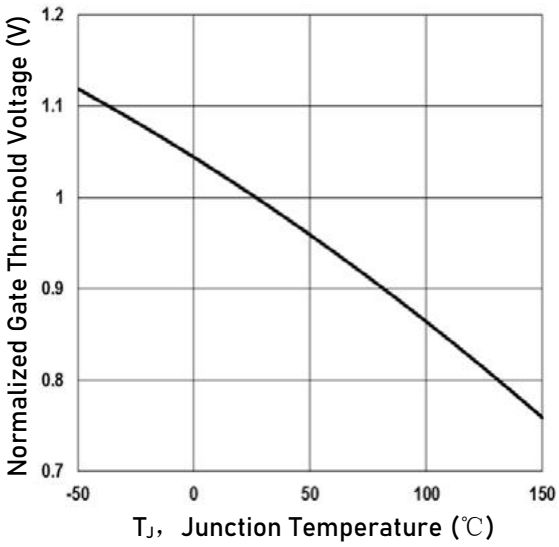


Fig.8 Normalized Vth vs. TJ

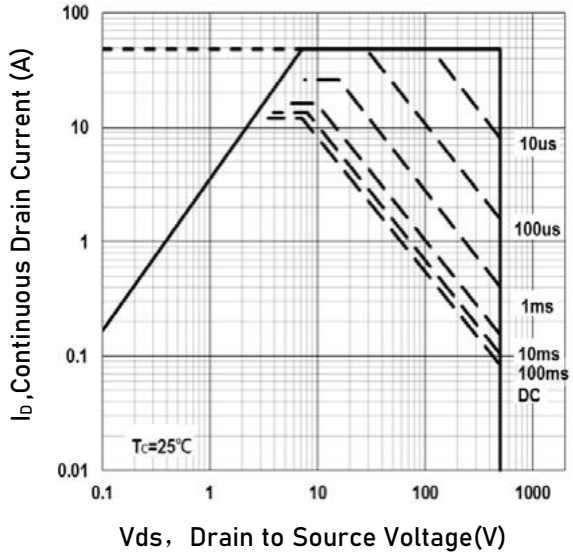


Fig.9 Safe Operating Area

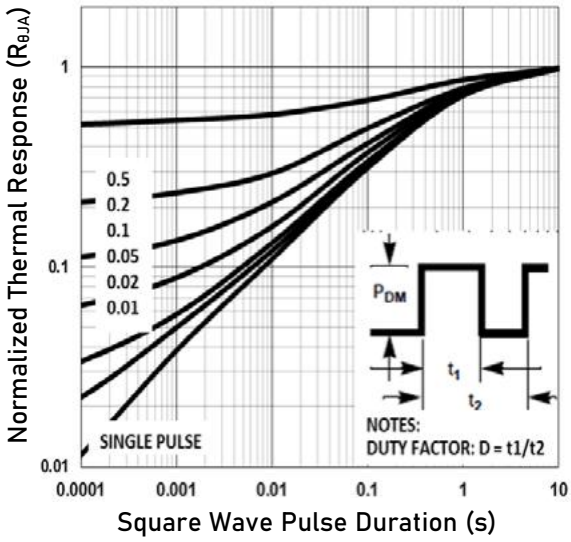
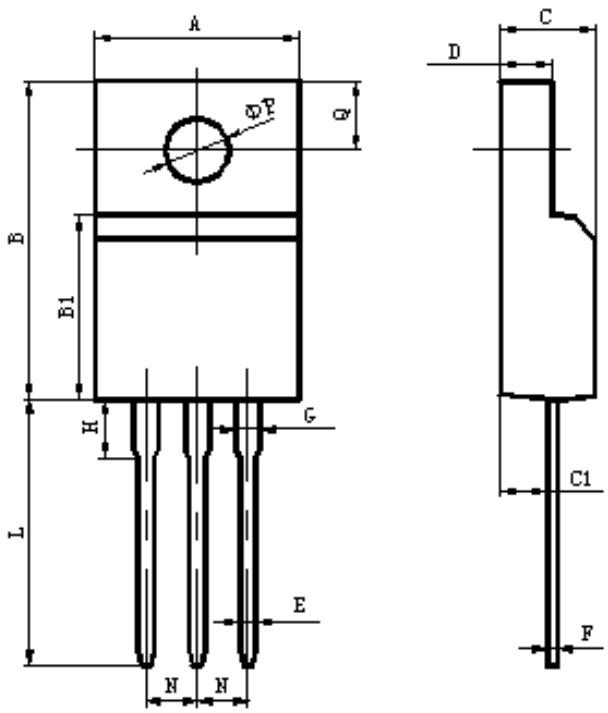


Fig.10 Transient Thermal Impedance

Package Mechanical Data-TO-220F Single



Items	Values(mm)	
	MIN	MAX
A	9.60	10.4
B	15.4	16.2
B1	8.90	9.50
C	4.30	4.90
C1	2.10	3.00
D	2.40	3.00
E	0.60	1.00
F	0.30	0.60
G	1.12	1.42
H	3.40	3.80
	2.40	2.90
L*	12.0	14.0
N	2.34	2.74
Q	3.15	3.55
Φ P	2.90	3.30